

AMENDMENTS TO THE CLAIMS

1. (Currently amended) A semiconductor apparatus, comprising:

a semiconductor substrate;

an electrode pad ~~including~~ comprising a metal layer and formed over the semiconductor substrate, said electrode pad providing contact between said semiconductor apparatus and external circuitry;

a MOS transistor formed over the semiconductor substrate; and

~~an analog~~ circuit formed over said semiconductor substrate and in a region under the electrode pad, ~~said analog circuit formed over the semiconductor substrate and~~ comprising a plurality of resistive elements ~~including~~ formed of a semiconductor material, said electrode pad being formed over said plurality of resistive elements.
2. (Currently amended) The semiconductor apparatus according to Claim 1, wherein the resistive elements ~~includes a specific~~ comprise a material made of one selected from the group consisting of polysilicon, silicon germanium, and silicon chrome.
3. (Currently amended) The semiconductor apparatus according to Claim 1, wherein the resistive elements include[[s]] a plurality of resistors connected serially.
4. (Currently amended) The semiconductor apparatus according to Claim 1, wherein the MOS transistor comprises a gate electrode ~~including a specific material of the resistive element~~ comprises a material selected from the group consisting of polysilicon, silicon germanium, and silicon chrome.

5. (Currently amended) The semiconductor apparatus according to Claim 1, further comprising:

an insulating film formed on the semiconductor substrate in a region in a vicinity of the electrode pad; and

a fuse element formed on the insulating film, said fuse element in electrical contact with said plurality of resistive elements.

6. (Currently amended) The semiconductor apparatus according to Claim 5, wherein the fuse element ~~includes a specific material of the resistive element~~ comprises a material selected from the group consisting of polysilicon, silicon germanium, and silicon chrome.

7. (Previously presented) The semiconductor apparatus according to Claim 5, further comprising:

a rerouting layer formed in a region above the fuse element; and

an external connection terminal formed on the rerouting layer in a region different from a formation region of the electrode pad.

8. (Currently amended) The semiconductor apparatus according to Claim 5, wherein the ~~[[analog]]~~ circuit comprises a voltage setting circuit, the resistive elements comprise~~[[s]]~~ at least two resistors for producing a split voltage based on an input source power voltage, and the voltage setting circuit changes the split voltage according to a condition of the fuse element.

9. (Currently amended) The semiconductor apparatus according to Claim 1, wherein the resistive elements comprise~~[[s]]~~ at least two resistors for producing a split voltage based on an input source power voltage, the ~~[[analog]]~~ circuit comprises a

reference voltage generator for generating a reference voltage and a voltage detector including a comparator for performing a comparison of the split voltage with the reference voltage.

10. (Currently amended) The semiconductor apparatus according to Claim 9, wherein the [[analog]] circuit further comprises an output driver for controlling an output voltage based on an input voltage, and the comparator of the voltage detector outputs a gate control voltage as a result of the comparison for controlling the output driver to control the output voltage.

11. – 16. (Canceled)

17. (Currently amended) The semiconductor apparatus according to Claim 1, wherein the resistive elements include[[s]] a plurality of doped semiconductor material resistors.

18. (Previously presented) The semiconductor apparatus according to Claim 4, wherein said gate electrode has lengthwise ends which are bent in an upward direction over an insulating film.